



AMENDED ABSTRACT

The present invention is a A method for producing a single crystal by Czochralski method with pulling a seed crystal from a raw material melt, wherein when in which a range of a pulling rate of pulling a single crystal is defined as V (mm/min), crystal, a temperature gradient at a solid-liquid interface is defined as G (K/mm) and a highest temperature at an interface between a crucible and a raw material melt is defined as T_{max} (°C), at least, a range of a value of V/G (mm²/K•min) including a desired defect region and/or a desired defect-free region is determined according to the T_{max} (°C), and are defined. The single crystal is pulled with controlling a value of V/G (mm²/K•min) the pulling rate and/or the temperature gradient at a solid-liquid interface within the determined range. There can be provided a The method for producing a single crystal in which when produces a single crystal is pulled with controlling a value of V/G , a value of V/G including in which a desired defect region and/or a desired defect-free region can be determined more precisely and a single crystal with desired quality can be more surely pulled.